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T Mar-la a	172 = -	Cooneh Mout	IDB	Timo stama
L Number	Hits 4859	Search Text ((29/25.01) or (438/99) or (438/795) or	DB USPAT;	Time stamp 2004/03/18 15:33
1	4859	((29/25.01) of (438/99) of (438/798) or (438/798) or	US-PGPUB	2004/03/18 13.33
		(438/799) or (257/40) or (257/421) or	05-10105	
		(257/422) or (257/424) or (361/805) or		
		(365/105) or (365/145) or (365/175)).CCLS.		
2	77		USPAT;	2004/03/18 15:38
	''	(438/796) or (438/797) or (438/798) or	US-PGPUB;	2001, 00, 20 20,00
		(438/799) or (257/40) or (257/421) or	EPO; JPO;	
		(257/422) or (257/424) or (361/805) or	DERWENT;	
		(365/105) or (365/145) or	IBM TDB	
		(365/175)).CCLS.) and (apparatus electric	_	
		adj field adj (generator modulator)) and		
		(pani polyanaline change adj of adj state		
		(conductive conducting) adj state		
		(semiconducting semiconductive) adj state		
		(non-conducting nonconducting		
,		non-conductive non-conductive insulating		
1,	1004	insulative) adj state) (apparatus electric adj field adj	USPAT;	2004/03/18 15:40
4	1004	(generator modulator)) and (pani	US-PGPUB;	2004,03/10 13.40
		polyanaline change adj of adj state	EPO; JPO;	
		(conductive conducting) adj state	DERWENT;	
		(semiconducting semiconductive) adj state	IBM TDB	
		(non-conducting nonconducting	_	
1		non-conductive non-conductive insulating		
1		insulative) adj state) and (thin adj film		
		tft ofet organic adj thin adj film adj		
		transistor organic adj field adj effect		
١	770	adj transistor)	HCDAM.	2004/03/18 15:41
5	772	(apparatus electric adj field adj (generator modulator)) and (pani	USPAT; US-PGPUB;	2004/03/18 13:41
		polyanaline change adj of adj state	EPO; JPO;	
		(conductive conducting) adj state	DERWENT;	
]	(semiconducting semiconductive) adj state	IBM TDB	
		(non-conducting nonconducting		
		non-conductive non-conductive insulating		
	ŀ	insulative) adj state) and (thin adj film		
		tft ofet organic adj thin adj film adj		
		transistor organic adj field adj effect		
		adj transistor) and (matrix matrices		
		three-dimensional "3D" interconnect		
6	45	interconnection array arrays)	USPAT;	2004/03/18 15:41
6	45	(apparatus electric adj field adj (generator modulator)) and (pani	US-PGPUB;	2004/03/18 13:41
		polyanaline change adj of adj state	EPO; JPO;	
		(conductive conducting) adj state	DERWENT;	
		(semiconducting semiconductive) adj state	IBM TDB	
		(non-conducting nonconducting	_	
		non-conductive non-conductive insulating	1	
		insulative) adj state) and (thin adj film		
		tft ofet organic adj thin adj film adj	1	
		transistor organic adj field adj effect		
		adj transistor) and (matrix matrices		
		three-dimensional "3D" interconnect		
		interconnection array arrays) and (interconnect interconnecting	1	
		interconnect interconnecting		
_	10	(("5043251").PN.) or (("5378916").PN.) or	USPAT;	2004/03/18 15:32
		(("5677041").PN.) or (("5537108").PN.) or	US-PGPUB;	
		(("5808351").PN.) or (("5686341").PN.) or	EPO; JPO;	
		(("5572409").PN.) or (("5371883").PN.) or	DERWENT;	
		(("5806995").PN.) or (("5825408").PN.)	IBM_TDB	
-	2	wo-9509438\$-\$.did.	USPĀT;	2002/12/01 16:19
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	L		IBM_TDB	

-	3	978043.ap.	USPAT;	2003/06/27 10:17
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	6	381994.ap.	USPAT;	2003/09/05 13:02
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1			DERWENT;	
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_	1	"4670768".PN.	USPAT	2003/06/27 10:43
_		"5937283".PN.	USPAT	2003/06/27 10:43
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_	1	"6015725".PN.	USPAT	2003/06/27 10:45
1_	1	"5757038".PN.	USPAT	2003/06/27 10:45
_	ī	"5723370".PN.	USPAT	2003/06/27 10:46
_	1	"5641694".PN.	USPAT	2003/06/27 10:46
_	1	"5480838".PN.	USPAT	2003/06/27 10:47
_	ī	"5308778".PN.	USPAT	2003/06/27 10:47
_	1	"5285093".PN.	USPAT	2003/06/27 10:47
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			DERWENT;	
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		(#5.6550.44.#) 707	IBM_TDB	0000/06/00 11 00
-	2	("5677041").PN.	USPAT;	2003/06/30 11:20
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			DERWENT;	
			IBM TDB	
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			EPO; JPO;	
			DERWENT;	
	i		IBM_TDB	
-	2	("5808351").PN.	USPAT;	2003/06/30 11:22
			US-PGPUB;	
]		EPO; JPO;	
1			DERWENT;	
		(HE CO CO (1 H) - Pro	IBM_TDB	0000100100
-	2	("5686341").PN.	USPAT;	2003/06/30 11:22
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
]_	2	("5572409").PN.	USPAT;	2003/06/30 11:23
1	'	(JUILIUJ / . IN .	US-PGPUB;	2003/00/30 11:23
			EPO; JPO;	
	[DERWENT;	
			IBM TDB	
-	2	("4371883").PN.	USPAT;	2003/06/30 11:23
	<u> </u>		US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
]		IBM_TDB	

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- 2 ("4806995").PN. EPO; JPO; DERWENT; IBM_TOB USPAT; US-FGFUB; EPO; JPO; DERWENT; EPO; JPO; JPO; DERWENT; EPO; JPO; JPO; DERWENT; EPO; JPO; JPO; DERWENT; EPO; JPO; JPO; DERWENT; EPO; JPO	-	2	(("5572409").PN.)	USPAT;	2003/06/30 11:24
- 2 ("4806995").PN.					
18M TOB	1				
2 ("4806995").PN. USFAT: US-FGUB; EPO, JPO; DERWENT; IEM TOB USFAT: USFAT; USFAT					
US-FGUUS FROM JPG DERMENT; IBM TOB USFAT; USF			/# 400 COOF #1 DV		0003/06/30 11:04
Property	-	2	("4806995").PN.		2003/06/30 11:24
Control Cont		1		1	
2					
2		l			
S-PGPUB; EPG; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPG; JPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPG; JPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; E		1	/!! 402 E 400 !! \ DN		2002/06/20 11.25
- 2 wo-9509438\$-\$.did.	-		("4825408").PN.	, ·	2003/06/30 11:23
- 2 wo-95094389-\$.did. DERWENT; IM TOB USPAT; US-FOFUB; EFO; JPO;					
TRM TOB USPAT: US-PGPUB; REPO; JPO; DERWERNT: IBM TOB USPAT: US-PG					
2 wo-95094388-\$.did. USFAT; 2003/06/30 11:26				· ·	
- 0 ep-0344346\$-\$.did. US-PGPUB; EPO; JPO; DERWENT; IBM TOB USPAT; US	_	2	wo-9509438\$-\$.did.		2003/06/30 11:26
Pep-0344346\$-\$.did. Sept.	ĺ	_	WO 35034504 4.did.		2003,00,30 11.20
- 0 ep-0344346\$-\$.did.					
- 0 ep-0344346\$-\$.did.					
- 0 ep-0344346\$-\$.did.					
- 2 ep-344346\$-\$.did. - 2 ep-344346\$-\$.did. - 0 reversible nearl2 change nearl2 conductivity nearl2 electric adj field and (thin adj film thin-film) - 14 change nearl2 conductivity nearl2 electric adj field and (thin adj film thin-film) - 10 change nearl2 conductivity nearl2 electric adj field and (438/\$9ccls. 257/\$9.ccls. 117/\$9.ccls.) - 10 change nearl2 conductivity nearl2 electric adj field and (438/\$9ccls. 257/\$9.ccls. 117/\$9.ccls.) - 15 pani and thin adj film adj transistor and (array matrix) - 1 pani and thin adj film adj transistor and (array matrix) and electric adj field near6 (conductivity resistivity) - 68 change nearl2 (conductivity resistivity) - 68 change nearl2 (conductivity resistivity) - 67 (438/776).CCLS. - 558 (438/795).CCLS.	-	0	ep-0344346\$-\$.did.		2003/06/30 11:27
Pep			· · · · ·		
- 2 ep-344346\$-\$.did. - 2 ep-344346\$-\$.did. - 3 reversible near12 change near12 conductivity near12 electric adj field and (thin adj film thin-film) (thin adj film thin-film) - 4 change near12 conductivity near12 electric adj field and (thin adj film thin-film) - 5 change near12 conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls. 117/\$9.ccls.) - 10 change near12 conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls. 117/\$9.ccls.) - 115 pani and thin adj film adj transistor and (array matrix) and electric adj field near6 (conductivity resistivity) - 68 change near12 (conductivity resistivity) - 68 change near12 (conductivity resistivity) near12 electric adj field near6 (conductivity resistivity) - 67 (438/776).CCLS. - 558 (438/795).CCLS.					
2 ep-344346\$-\$.did.		}		1	
2 ep-344346\$-\$.did.					
- 0 reversible near12 change near12 conductivity near12 electric adj field and (thin adj film thin-film) (thin adj film adj transistor and (thin adj f	-	2	ep-344346\$-\$.did.		2003/06/30 11:28
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PG				US-PGPUB;	
Teversible near12 change near12 conductivity near12 electric adj field and (thin adj film thin-film) Conductivity near12 electric adj field and (thin adj film thin-film) Conductivity near12 electric adj field and (thin adj film thin-film) Conductivity near12 electric adj field and (thin adj film thin-film) Conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls. Conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls. Conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls. Conductivity near12 electric adj field and (array matrix) Conductivity near12 electric adj field and (array matrix) Conductivity near12 electric adj field Conductivity near12 Conductivity near12 Conductivity near12 Conductivity near				EPO; JPO;	
Conductivity near12 change near12				DERWENT;	
Conductivity near12 electric adj field and (thin adj film thin-film)					
Change near12 conductivity near12 electric adj field and (thin adj film thin-film)	-	0		· ·	2004/03/15 20:48
- 14 change near12 conductivity near12 electric adj field and (thin adj film thin-film)					
- 14 change near12 conductivity near12 electric adj field and (thin adj film thin-film) - 10 change near12 conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls. 117/\$9.ccls.) - 115 pani and thin adj film adj transistor and (array matrix) - 1 pani and thin adj film adj transistor and (array matrix) and electric adj field near6 (conductivity resistivity) - 68 change near12 (conductivity resistivity) - 67 (438/776).CCLS. - 558 (438/795).CCLS. 1 change near12 conductivity near12 electric adj field near6 (2003/09/05 11:10 USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT			(thin adj film thin-film)		
- 10 change near12 conductivity near12 electric adj field and (thin adj film thin-film) USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; ISM TDB USPĀT; US-PGPUB; EPO					
adj field and (thin adj film thin-film) Change near12 conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls. 117/\$9.ccls.) pani and thin adj film adj transistor and (array matrix) pani and thin adj film adj transistor and (array matrix) and electric adj field near6 (conductivity resistivity) change near12 (conductivity resistivity) change near12 (conductivity resistivity) change near12 (conductivity resistivity) change near12 (conductivity resistivity) and electric adj field near12 electric adj field near12 electric adj field near12 electric adj field near12 electric adj field uspĀT; us-pGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;		١,,			0000/00/05 11 06
- 10 change near12 conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT;	-	14			2003/09/05 11:06
- 10 change near12 conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DE			adj field and (thin adj film thin-film)		
- 10 change near12 conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls.) - 115 pani and thin adj film adj transistor and (array matrix) - 1 pani and thin adj film adj transistor and (array matrix) us-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;					
- 10 change near12 conductivity near12 electric adj field and (438/\$9ccls. 257/\$9.ccls. 117/\$9.ccls.) - 115 pani and thin adj film adj transistor and (array matrix) - 1 pani and thin adj film adj transistor and (array matrix) and electric adj field near6 (conductivity resistivity) - 68 change near12 (conductivity resistivity) - 68 change near12 (conductivity resistivity) - 67 (438/776).CCLS. - 558 (438/795).CCLS. 10 change near12 electric adj field					
adj field and (438/\$9ccls. 257/\$9.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	_	10	change nearly conductivity nearly electric		2003/09/05 11:14
117/\$9.ccls.) Pani and thin adj film adj transistor and (array matrix) pani and thin adj film adj transistor and (array matrix) and electric adj field near6 (conductivity resistivity) change near12 (conductivity resistivity) change near12 (conductivity resistivity) near12 electric adj field change near12 (conductivity resistivity) change near12 (conductivit		10			2003,03,03 11.11
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 115 pani and thin adj film adj transistor and (array matrix) 2003/09/05 11:15 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;			,		
- 115 pani and thin adj film adj transistor and (array matrix)					
(array matrix)	-	115	pani and thin adj film adj transistor and		2003/09/05 11:15
- 1 pani and thin adj film adj transistor and (array matrix) and electric adj field near6 (conductivity resistivity) - 68 change near12 (conductivity resistivity) - 68 change near12 (conductivity resistivity) - 67 (438/776).CCLS. - 558 (438/795).CCLS. EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 1 pani and thin adj film adj transistor and (array matrix) and electric adj field near6 (conductivity resistivity) - 68 change near12 (conductivity resistivity) - 67 (438/776).CCLS. - 67 (438/795).CCLS. 18M_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			· ·		
- 1 pani and thin adj film adj transistor and (array matrix) and electric adj field near6 (conductivity resistivity) - 68 change near12 (conductivity resistivity) - 67 (438/776).CCLS. - 558 (438/795).CCLS. Denum TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;				DERWENT;	
(array matrix) and electric adj field				IBM_TDB	
near6 (conductivity resistivity)	-	1			2003/09/05 11:17
- 68 change near12 (conductivity resistivity)					
- 68 change near12 (conductivity resistivity) near12 electric adj field USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			near6 (conductivity resistivity)		
- 68 change near12 (conductivity resistivity) near12 electric adj field US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
near12 electric adj field US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			10 / 1 / 1 / 1 / 1		0000/00/05 10 55
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-	68			2003/09/05 13:01
- 67 (438/776).CCLS. DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			neariz electric adj field		
- 67 (438/776).CCLS. IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
- 67 (438/776).CCLS. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	l _	67	(438/776) CCLS		2003/00/05 17.22
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; DERWENT;		"	(100) 110) .0000.		2003/03/03 17:33
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 558 (438/795).CCLS. IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; DERWENT;					
- 558 (438/795).CCLS. USPĀT; 2003/09/05 17:33 US-PGPUB; EPO; JPO; DERWENT;					
US-PGPUB; EPO; JPO; DERWENT;	_	558	(438/795).CCLS.		2003/09/05 17:33
EPO; JPO; DERWENT;			•		
DERWENT;					
				IBM_TDB	

<u> </u>	558	(438/795).CCLS.	USPAT;	2003/09/05 17:33
-	330	(4307793).0015.	US-PGPUB;	2000,03,00 1,.00
			EPO; JPO;	
	15	(photochemical polyaniline photochemistry)	IBM_TDB USPAT;	2003/09/05 17:39
-	15	and ((438/795).CCLS.)	US-PGPUB;	2003/09/03 17.39
		4.100, 130, 130, 130, 130, 130, 130, 130,	EPO; JPO;	
			DERWENT;	
	29	(430/707) CCTC	IBM_TDB USPAT;	2003/09/05 17:41
-	29	(438/797).CCLS.	US-PGPUB;	2003/03/03 17.41
			EPO; JPO;	
			DERWENT;	
	302	(438/798).CCLS.	IBM_TDB USPAT;	2003/09/05 17:42
	302	(4307730).0013.	US-PGPUB;	2003/03/03 17.42
			EPO; JPO;	
			DERWENT;	
	1688	(438/796).CCLS.	IBM_TDB USPAT;	2003/09/05 17:42
-	1000	(438/790).CCLS.	US-PGPUB;	2003/03/03 17.42
			EPO; JPO;	
			DERWENT;	
_	2518	((438/796).CCLS.) ((438/798).CCLS.)	IBM_TDB USPAT;	2003/09/05 17:42
~	2310	((438/797).CCLS.) ((438/795).CCLS.)	US-PGPUB;	2003/03/03 17.42
		((100,000,000,000,000,000,000,000,000,00	EPO; JPO;	
			DERWENT;	
_	41	(((438/796).CCLS.) ((438/798).CCLS.)	IBM_TDB USPAT;	2003/09/05 18:05
	41	((438/797).CCLS.) ((438/795).CCLS.)) and	US-PGPUB;	2003/03/03 10:03
		(electric adj field or (photochemical	EPO; JPO;	
		photochemistry)) and (matrix array)	DERWENT;	
_	0	 (gmr giant adj magnetic adj resonance)	IBM_TDB USPAT;	2003/09/05 18:07
	Ĭ	near12 electric adj field near12	US-PGPUB;	2003/03/03 10:07
	·	(semiconducting semiconductor insulator	EPO; JPO;	
		insualting) near12 (conductor conductive)	DERWENT; IBM TDB	
_	2	 (gmr giant adj magnetic adj resonance)	USPAT;	2003/09/05 18:07
	_	near12 electric adj field	US-PGPUB;	2000, 05, 00 2000
			EPO; JPO;	
			DERWENT; IBM TDB	
_	15	"5043251"	USPAT;	2003/09/12 14:10
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	1	("5043251").PN.	USPAT	2003/09/12 15:18
_	183	apparatus.ti,ab,clm. and (fabricating	USPAT;	2004/03/15 13:50
		fabrication) near12 method near12 (thin	US-PGPUB;	
		adj film adj transistor tft otft misfet mosfet mos adj transistor mis adj	EPO; JPO; DERWENT;	
		transistor organic adj tft)	IBM_TDB	
-	3	apparatus.ti,ab,clm. and (fabricating	USPĀT;	2004/03/15 13:25
		fabrication) near12 method near12 (thin	US-PGPUB;	
		adj film adj transistor tft otft misfet mosfet mos adj transistor mis adj	EPO; JPO; DERWENT;	
		transistor organic adj tft) and	IBM_TDB	
	1504	118/\$9.ccls.	IICDAM -	2004/02/15 17 00
-	1564	((438/99) or (438/776) or (438/795) or (438/796) or (438/797) or (438/798) or	USPAT; US-PGPUB	2004/03/15 17:08
		(438/799)).CCLS.		
-	372	(((438/99) or (438/776) or (438/795) or	USPAT;	2004/03/15 13:52
		(438/796) or (438/797) or (438/798) or (438/799)).CCLS.) and (interconnect	US-PGPUB;	
		interconnection stack stacked)	EPO; JPO; DERWENT;	
	!		IBM_TDB	

_	98	(((438/99) or (438/776) or (438/795) or	USPAT;	2004/03/15 15:03
		(438/796) or (438/797) or (438/798) or	US-PGPUB;	
		(438/799)).CCLS.) and (interconnect	EPO; JPO;	
	ĺ	interconnection stack stacked) and	DERWENT;	
		(ultraviolet ultra-violet uv)	IBM_TDB	
-	24369	apparatus.ti,ab,clm. and semiconductor adj	USPAT;	2004/03/15 14:20
		device.ti,ab,clm.	US-PGPUB;	
			EPO; JPO;	
-			DERWENT;	
			IBM_TDB	
-	25	apparatus.ti,ab,clm. and semiconductor adj	USPAT;	2004/03/15 14:22
		device.ti,ab,clm. and misfet.ti,ab,clm.	US-PGPUB;	
			EPO; JPO;	
	1	,	DERWENT;	
			IBM_TDB	
-	219	apparatus.ti,ab,clm. and semiconductor adj	USPAT;	2004/03/15 14:23
		device.ti,ab,clm. and (mosfet	US-PGPUB;	
		misfet).ti,ab,clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	200	apparatus.ti,ab,clm. and semiconductor adj	USPAT;	2004/03/15 14:23
		device.ti,ab,clm. and mosfet.ti,ab,clm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	0	(((438/99) or (438/776) or (438/795) or	USPAT;	2004/03/15 15:04
	İ	(438/796) or (438/797) or (438/798) or	US-PGPUB;	
		(438/799)).CCLS.) and (interconnect	EPO; JPO;	
	}	interconnection stack stacked) and	DERWENT;	
		(electric adj field near6 (conductivity	IBM_TDB	
		resistivity))	_	
-	6	(US-6458621-\$ or US-6696312-\$ or	USPAT;	2004/03/15 15:22
		US-6635406-\$ or US-6331356-\$ or	US-PGPUB	
		US-5840622-\$).did. or		
	ļ	(US-20020151117-\$).did.		
-	0	polymer near2 (integrated adj circuit ic)	USPAT;	2004/03/15 15:23
		near6 electrochemical	US-PGPUB	
-	2	polymer near2 (integrated adj circuit ic)	USPAT;	2004/03/15 15:25
		and electrochemical.ti,ab,clm.	US-PGPUB	
-	1	electrochemical near2	USPAT;	2004/03/15 15:54
<u> </u>		patterning.ti,ab,clm.	US-PGPUB;	
			EPO; JPO;	
i			DERWENT;	
1	_		IBM_TDB	
-	2	("5572409").PN.	USPAT;	2004/03/15 15:58
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
Ī	_	(11 00442206 6 343 11) 727	IBM_TDB	2004/02/15 15:50
-	0	("wo-9944229\$-\$.did.").PN.	USPAT;	2004/03/15 15:59
1	j		US-PGPUB;	
1	1		EPO; JPO;	
1			DERWENT;	
	_	(11:00 000443306 6 4:4 11) 703	IBM_TDB	2004/02/15 15:50
-	0	("wo-99044229\$-\$.did.").PN.	USPAT;	2004/03/15 15:59
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
i _	,	("QQQ4422Q") DN	IBM_TDB	2004/03/15 15:59
1 -	1	("99044229").PN.	EPO; DERWENT	2004/03/13 13:59
_	3	("9944229").PN.	EPO;	2004/03/15 16:09
-	3	())11244 . F.W.	DERWENT	2004/03/13 10:09
l _	1	("5537108").PN.	USPAT	2004/03/15 16:33
_	0	("apparatusnear6programmablenear6(fuseantif		
	l ,	/ apparacusmearoprogrammantemearo(tuseametri	US-PGPUB;	A ~ A ~ E M A 3 \ T A T D ! 3 3
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
I	1		TUE 1 DD	<u> </u>

-	54	apparatus near6 programmable near6 (fuse	USPAT;	2004/03/15 16:34
		antifuse anti-fuse)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
İ_	44	apparatus near6 programmable near6 (fuse	USPAT;	2004/03/15 16:38
	''	antifuse anti-fuse).ti,ab,clm.	US-PGPUB;	2001,00,10 10.00
			EPO; JPO;	
			DERWENT;	
	•		IBM_TDB	
-	2676	H01L\$6.ipc. and programmable.ti.	USPAT;	2004/03/15 16:58
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	407	H01L\$6.ipc. and programmable.ti. and	USPAT;	2004/03/15 16:59
		interconnect\$3.ti,ab,clm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	191	H01L021\$6.ipc. and programmable.ti. and	USPAT;	2004/03/15 17:00
		interconnect\$3.ti,ab,clm.	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	H01L021/64.ipc. and programmable.ti. and	USPAT;	2004/03/15 17:00
		interconnect\$3.ti,ab,clm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	386	H01L021/64.ipc.	USPAT;	2004/03/15 17:13
	<u> </u>		US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	2	H01L051/80.ipc.	USPAT;	2004/03/15 17:02
	_		US-PGPUB;	2001,00,10 11102
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
_	1	matrix near6 electrode.ti,ab,clm. and	USPĀT;	2004/03/15 17:09
		programmable near3 (fuse anti-fuse anti adj fuse antifuse)	US-PGPUB; EPO; JPO;	
		adj iuse anciiuse)	DERWENT;	
			IBM TDB	
-	2099	(29/25.01).CCLS.	USPAT;	2004/03/15 17:14
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1_	0	(29/25.01and(electrodeelectrodes)near6(arra	IBM_TDB	
-		(29,23.01and(erectrodeerectrodes) hearo(arra)	US-PGPUB;	INTROGET OF LEGICAL TO CARDIO
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
1-	30	29/25.01 and (electrode electrodes) near6	USPAT;	2004/03/15 17:16
1		(array matrix perpendicular)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	456	(29/25.01).CCLS.	USPAT;	2004/03/15 18:59
	.55	,==, ==, ====	US-PGPUB	_ 111, 10, 10 10, 05
-	239	(438/99).CCLS.	USPAT;	2004/03/15 19:48
1			US-PGPUB	
-	81	(438/776).CCLS.	USPAT;	2004/03/15 19:55
	636	(420/705) 607.5	US-PGPUB	0004/00/15 10 55
[-	638	(438/795).CCLS.	USPAT;	2004/03/15 19:55
_	202	(438/796).CCLS.	US-PGPUB USPAT;	2004/03/15 19:55
1	202	(430/130).0013.	US-PGPUB	2004/03/13 13:33
-	30	(438/797).CCLS.	USPAT;	2004/03/15 19:55
		•	US-PGPUB	

	214	L (430 (700) CGT C	I ricoam.	2004/03/15 19:55
-	314	(438/798).CCLS.	USPAT; US-PGPUB	2004/03/15 19:55
-	181	(438/799).CCLS.	USPAT; US-PGPUB	2004/03/15 19:55
-	1249	((438/795).CCLS.) ((438/796).CCLS.) ((438/797).CCLS.) ((438/798).CCLS.) ((438/799).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/15 19:55
_	29	(((438/795).CCLS.) ((438/796).CCLS.) ((438/797).CCLS.) ((438/798).CCLS.) ((438/799).CCLS.)) and (electrode electrodes) near12 (electric adj field	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/15 19:57
-	59	electric adj fields ultraviolet ultra-violet ultra adj violet uv) (US-6261637-\$ or US-6280585-\$ or US-5858462-\$ or US-6413845-\$ or US-6448492-\$ or US-6140025-\$ or	IBM_TDB USPAT; US-PGPUB; EPO; DERWENT	2004/03/15 20:20
		US-5696008-\$ or US-5937283-\$ or US-4670768-\$ or US-6461900-\$ or US-5043251-\$ or US-5371883-\$ or US-5378916-\$ or US-557708-\$ or US-5572409-\$ or US-5677041-\$ or US-5806995-\$ or US-5686341-\$ or US-5808351-\$ or US-5825408-\$ or US-4825408-\$ or US-4806995-\$ or US-6429450-\$ or US-6544902-\$ or US-6331356-\$ or US-644902-\$ or US-6331356-\$ or US-6458621-\$ or US-6458621-\$ or US-6455359-\$ or US-3829881-\$).did. or (US-20020127833-\$ or US-20020136823-\$ or US-20020153149-\$ or US-20020136823-\$ or US-20020153149-\$ or US-20020151117-\$ or US-20020149107-\$ or US-20020151117-\$ or US-20020149107-\$ or US-20020151117-\$ or US-20020149107-\$ or US-20020057398-\$ or US-20030099845-\$).did. or (WO-9509438-\$ or WO-9944229-\$).did. or (US-5858462-\$ or US-5043251-\$ or US-5656548-\$ or US-572409-\$ or US-4371883-\$ or US-5686341-\$ or US-5537108-\$ or US-5677041-\$ or US-59191315-\$).did.	DERWENT	
-	2		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/15 20:55
-	2	("5686341").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/15 21:00
-	0	w0-9509438\$-\$.did.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/15 21:00
-	2	wo-9509438\$-\$.did.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/15 21:01

				····
_	60	(US-4825408-\$ or US-4806995-\$ or	USPAT;	2004/03/15 21:14
		US-5716218-\$ or US-6544902-\$ or	US-PGPUB;	
		US-6429450-\$ or US-5808351-\$ or	EPO;	
		US-6280585-\$ or US-5858462-\$ or	DERWENT	
		US-3829881-\$ or US-6455359-\$ or		
		US-5840622-\$ or US-6331356-\$ or		
		US-6458621-\$ or US-6635406-\$ or US-6696312-\$ or US-5686341-\$ or		ľ
	ŀ	US-5677041-\$ or US-5806995-\$ or		
		US-6448492-\$ or US-6140025-\$ or		
		US-6413845-\$ or US-6261637-\$ or		
		US-5825408-\$ or US-4371883-\$ or		
		US-4670768-\$ or US-5043251-\$).did. or		
		(US-5371883-\$ or US-5378916-\$ or		
	i	US-5572409-\$ or US-5537108-\$ or		
		US-5937283-\$ or US-5696008-\$ or		1
		US-6461900-\$).did. or (US-20010023771-\$ or		
		US-20040040131-\$ or US-20040009650-\$ or		1
		US-20030085439-\$ or US-20020136823-\$ or		
1		US-20030099845-\$ or US-20020057398-\$ or		
		US-20030119287-\$ or US-20030092267-\$ or	1	
		US-20020149107-\$ or US-20020151117-\$ or		
	1	US-20020127833-\$ or US-20020153149-\$).did.		
		or (WO-9944229-\$ or WO-9509438-\$).did. or		
		(US-4806995-\$ or US-5677041-\$ or	I	
		EP-159397-\$ or US-6432739-\$ or	1]
		US-5537108-\$ or US-5858462-\$ or		
		JP-59191315-\$ or US-5686341-\$ or		
		US-4371883-\$ or US-5572409-\$ or		
	_	US-5043251-\$ or US-5656548-\$).did.		
-	1	','	USPAT;	2004/03/15 21:15
		US-5716218-\$ or US-6544902-\$ or	US-PGPUB;	
		US-6429450-\$ or US-5808351-\$ or	EPO; JPO;	‡
		US-6280585-\$ or US-5858462-\$ or	DERWENT;	
		US-3829881-\$ or US-6455359-\$ or	IBM_TDB	
		US-5840622-\$ or US-6331356-\$ or US-6458621-\$ or US-6635406-\$ or	ľ	
		US-6696312-\$ or US-5686341-\$ or		
		US-5677041-\$ or US-5806995-\$ or		
		US-6448492-\$ or US-6140025-\$ or		
		US-6413845-\$ or US-6261637-\$ or		
		US-5825408-\$ or US-4371883-\$ or		!
	1	US-4670768-\$ or US-5043251-\$).did. or]
		(US-5371883-\$ or US-5378916-\$ or		
		US-5572409-\$ or US-5537108-\$ or		
		US-5937283-\$ or US-5696008-\$ or	1	
		US-6461900-\$).did. or (US-20010023771-\$ or	1	
		US-20040040131-\$ or US-20040009650-\$ or	1	
		US-20030085439-\$ or US-20020136823-\$ or	İ	
		US-20030099845-\$ or US-20020057398-\$ or	1	
1	1	US-20030119287-\$ or US-20030092267-\$ or		
		US-20020149107-\$ or US-20020151117-\$ or		
	1	US-20020127833-\$ or US-20020153149-\$).did.		
	1	or (WO-9944229-\$ or WO-9509438-\$).did. or		
		(US-4806995-\$ or US-5677041-\$ or		
		EP-159397-\$ or US-6432739-\$ or US-5537108-\$ or US-5858462-\$ or		
		US-553/108-5 or US-5858462-5 or		
	1	US-4371883-\$ or US-5572409-\$ or		
	1	US-5043251-\$ or US-5656548-\$).did.) and		
		sonnenschein.in.		
l _	4085		USPAT;	2004/03/15 21:18
ŀ		(257/776) or (257/6) or (257/432) or	US-PGPUB	2001,00,10 21.10
		(257/739) or (438/130) or (361/805)).CCLS.		
_	332	(((257/421) or (257/421) or (257/758) or	USPAT;	2004/03/15 21:19
		(257/776) or (257/6) or (257/432) or	US-PGPUB;	
		(257/739) or (438/130) or	EPO; JPO;	
		(361/805)).CCLS.) and (pani polyaniline uv	DERWENT;	
i	1	ultraviolet ultra-violet ultra adj violet)	IBM TDB	

_	25	(((257/421) or (257/421) or (257/758) or (257/776) or (257/6) or (257/432) or	USPAT; US-PGPUB;	2004/03/15 21:20
		(257/739) or (438/130) or (361/805)).CCLS.) and (pani polyaniline uv	EPO; JPO; DERWENT;	
		ultraviolet ultra-violet ultra adj violet electric adj field) and (conductive	IBM_TDB	
-	56		USPAT;	2004/03/15 21:28
		(257/776) or (257/6) or (257/432) or (257/739) or (438/130) or	US-PGPUB; EPO; JPO;	
		(361/805)).CCLS.) and (pani polyaniline uv ultraviolet ultra-violet ultra adj violet	DERWENT; IBM_TDB	
	1106	electric adj field) and (conductive conduction) near12 (state resistive)	HCDAM.	2004/03/15 21:28
-	1106	(257/40).CCLS.	USPAT; US-PGPUB; EPO; JPO;	2004/03/13 21.28
			DERWENT; IBM TDB	
-	457	((257/40).CCLS.) and (apparatus method).ti,ab,clm.	USPAT; US-PGPUB;	2004/03/15 21:29
	=	meeriod). Ci, ab, Cim.	EPO; JPO; DERWENT;	
_	394	(((257/40).CCLS.) and (apparatus	IBM_TDB USPAT;	2004/03/15 21:29
		method).ti,ab,clm.) not (((438/99) or (438/776) or (438/795) or (438/796) or	US-PGPUB; EPO; JPO;	
		(438/797) or (438/798) or (438/799)).CCLS.)	DERWENT; IBM TDB	
-	361		USPĀT; US-PGPUB	2004/03/16 16:05
-	6	(array matrix matrices) near6 (electrode	USPAT; US-PGPUB;	2004/03/16 15:41
		electrodes)	EPO; JPO; DERWENT;	
_	153	(257/422).CCLS.	IBM_TDB USPAT;	2004/03/16 16:05
-	64	(US-5371883-\$ or US-5043251-\$ or US-5378916-\$ or US-5537108-\$ or	US-PGPUB USPAT; US-PGPUB;	2004/03/16 16:15
		US-5572409-\$ or US-5677041-\$ or US-5806995-\$ or US-5686341-\$ or	EPO; DERWENT	
		US-6331356-\$ or US-6429450-\$ or US-6458621-\$ or US-6635406-\$ or	DERWENT	:
		US-6696312-\$ or US-5808351-\$ or US-5825408-\$ or US-3340463-\$ or		
		US-3593045-\$ or US-4667391-\$ or US-5179429-\$ or US-5858462-\$ or		
		US-6140025-\$ or US-6261637-\$ or US-6280585-\$ or US-6413845-\$ or		
		US-6448492-\$ or US-5840622-\$).did. or (US-3829881-\$ or US-4825408-\$ or		
		US-6544902-\$ or US-5716218-\$ or US-4371883-\$ or US-6455359-\$ or		
		US-5937283-\$ or US-4670768-\$ or US-5696008-\$ or US-6461900-\$ or		
		US-4806995-\$).did. or (US-20030085439-\$ or US-20020151117-\$ or US-20020127833-\$ or		
		US-20010023771-\$ or US-20020153149-\$ or US-20040009650-\$ or US-20040040131-\$ or US-20030099845-\$ or US-20020057398-\$ or		
		US-20030099843-\$ or US-20020037398-\$ or US-20020136823-\$ or US-20020149107-\$ or US-20030092267-\$ or US-20030119287-\$).did.		
		or (WO-9944229-\$ or WO-9509438-\$).did. or (US-5656548-\$ or US-6432739-\$ or		
		JP-59191315-\$ or US-5858462-\$ or EP-159397-\$ or US-4806995-\$ or		
		US-4371883-\$ or US-5572409-\$ or US-5686341-\$ or US-5537108-\$ or		
		US-5677041-\$ or US-5043251-\$).did.	<u> </u>	

-	160	parallel adj (strips electrodes) and	USPAT;	2004/03/16 16:29
		365/\$9.ccls.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	29		USPAT;	2004/03/16 16:30
		(perpendicularly perpendicular orthogonal	US-PGPUB;	
		orthogonally) and 365/\$9.ccls.	EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	4	(US-6498744-\$ or US-6670659-\$ or	USPĀT	2004/03/16 16:43
		US-6055180-\$ or US-6236587-\$).did.		
-	163	(365/105).CCLS.	USPAT;	2004/03/16 16:43
			US-PGPUB	
-	1151	(365/145).CCLS.	USPAT;	2004/03/16 16:43
			US-PGPUB	
-	320	(365/175).CCLS.	USPAT;	2004/03/16 16:43
			US-PGPUB	
_	1579	((365/105).CCLS.) ((365/145).CCLS.)	USPAT;	2004/03/16 16:44
		((365/175).CCLS.)	US-PGPUB;	
		((000, 110, 00010)	EPO; JPO;	
1			DERWENT;	
			IBM TDB	
<u> </u>	16	(((365/105).CCLS.) ((365/145).CCLS.)	USPAT;	2004/03/16 18:36
		((365/175).CCLS.)) and parallel near6	US-PGPUB;	=====================================
		(electrodes strips plates) near12	EPO; JPO;	
		(orthogonal orthogonally perpedicular	DERWENT;	
		perpendicularly)	IBM TDB	
<u>_</u>	0	parallel near6 (electrodes strips plates)	USPAT;	2004/03/16 18:40
		near12 (orthogonal orthogonally	US-PGPUB;	2004/03/10 10:40
		perpedicular perpendicularly) and	EPO; JPO;	
		(polyaniline pani) and (ultraviolet	DERWENT;	
		ultra-violet ultra adj violet)	IBM TDB	
1_	17	parallel near6 (electrodes strips plates)	USPAT;	2004/03/16 18:41
	'	near12 (orthogonal orthogonally	US-PGPUB;	2004/03/10 10:41
		perpedicular perpendicularly) and	EPO; JPO;	
		(polyaniline pani)	DERWENT;	
		(poryamiline pani)	IBM TDB	
l _	2	("3586415").PN.	USPAT;	2004/03/17 13:42
-	-	(3300413).EN.	US-PGPUB;	2004/03/17 13.42
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
1_	2	("5667041").PN.	USPĀT;	2004/03/17 13:43
	_	(3007041 /:IN:	US-PGPUB;	2004/03/17 13:43
			EPO; JPO;	' ·
			DERWENT;	
			IBM TDB	
_	2	("5677041").PN.	USPAT;	2004/03/17 13:43
		(00//071 /.LN.	US-PGPUB;	2004/03/17 13:43
			EPO; JPO;	
			DERWENT;	
			IBM TDB]
_	5	012023.ap.	USPAT:	2004/03/17 17:02
_	3	012023.ap.	US-PGPUB;	2004/03/1/ 1/:02
			EPO; JPO;	
			DERWENT;	
			I -	
_	2	("5742074").PN.	IBM_TDB USPAT;	2004/03/17 17:21
		(0/120/7).LN.	US-PGPUB;	2004/03/11 11:21
			EPO; JPO;	
			DERWENT; IBM TDB	
1_	1063	(257/48).CCLS.	_	2004/02/17 17:22
-	1003	(201/40).0005.	USPAT;	2004/03/17 17:22
			US-PGPUB;	
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-	22	((257/48).CCLS.) and (bus bus-line bus adj	USPAT;	2004/03/17 17:	23
		line) and display and (monitor monitoring	US-PGPUB;		
		test testing)	EPO; JPO;		
			DERWENT;		
			IBM TDB		
_	23	((257/48).CCLS.) and (bus bus-line bus adj	USPAT;	2004/03/17 17:	23
		line) and display and (inspect inspecting	US-PGPUB;		
		monitor monitoring test testing)	EPO; JPO;		
		<u>-</u>	DERWENT;		
	ŀ		IBM TDB		